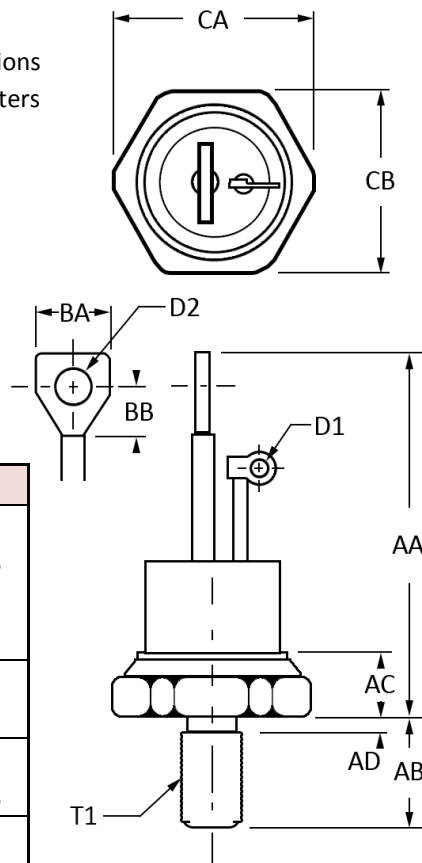




IMAGE SERVES AS A REPRESENTATION OF THE PACKAGE STYLE ONLY

MECHANICAL SPECIFICATIONS

Note:
All dimensions are in millimeters



	mm
AA	39.0 Max
AB	11.0 ± 0.5
AC	4.0 ± 0.5
AD	2.2 Max
BA	8.0
BB	4.0 Max
CA	21.0
CB	19.0 ± 0.3
D1	Ø1.8
D2	Ø3.6
T1	M6 x 1.0

ABSTRACT

The 29RD60 is a general purpose p-n-p-n silicon control rectifier used primarily for switching. The thyristor is enclosed in a hermetically sealed NI-2 metal stud package, which contributes to the durability and longevity of the device.

ELECTRICAL CHARACTERISTICS

V _{RSM}	V _{RRM}	I _{T(AV)}		I _{TSM} (50 Hz)	I ² t t=2-10ms (A ² S)	P _{GM}	P _{G(AV)}	V _{GRM}	I _{GFM}	T _J	T _{stg}	I _{RRM} / I _{DRM}	
		A	T _C (°C)									(mA)	T _J (°C)
700	600	26.0	88	500	1250.00	5.0	0.50	5.0	2.0	125	-40~125	10.0	125

V _{TM}	V _{GT}		I _{GT}		V _{GD} (min)			dv/dt (min)			I _H Typ. (mA)	R _{th} (°C/W)	Pkg.	
	T _J (°C)	I _{TM} (A)	(V)	(mA)	(V)	T _J (°C)	V _D (V)	(V/μs)	T _J (°C)	V _D (V)				
1.92	25	80	2.5	50.00	25	0.20	125	2/3V _{DRM}	200	125	2/3V _{DRM}	70	0.8000	NI-2